IN THE SPECIFICATION

Please amend the specification as follows. Added matter is underlined and deleted matter is struckthrough or shown in double brackets, i.e., [[ ]].

Please replace the paragraph beginning on page 1 at line 25 with the following:

Here, in the active matrix type display device, a plurality of data lines and a plurality of select lines which cross respective data lines at right angles, are provided, and pixels are provided on respective crossing points of the data lines and the select lines. When a case of using the OLED as the optical modulation element is used as an example, as shown in FIG. 18, a select module 113 is conducted only in a select period in which a select line 103 is outputting a select signal SEL of a select level, and the select module 113 connects a data line 102 to a drive module 111 which drives the OLED 112.

Please replace the paragraph beginning on page 6 at line 9 with the following:

Note that, according to a structure of the prior art, in a case where dispersion occurs in a threshold value characteristic of the drive switching element (TFT 121), which drives the optical modulation element, due to the dispersion brought about in manufacturing at a time when many pixels are formed, there occurs such a problem that luminance, which should be uniform~~uniformed~~, becomes hetereogeneous~~ununiformed~~ to a large extent.

Please replace the paragraph beginning on page 7 at line 1 with the following:

On the other hand, in the present invention~~invenetion~~, since an output of the output inverter, which functions as an output end of the memory element, is directly connected to one end of the optical modulation element, variation of the luminance level of the optical modulation element, which is brought about by variation of a characteristic of the drive switching element, does not occur, even though the

dispersion occurs in manufacturing, so that it is possible to light the optical modulation element at a constant luminance level.

Please replace the paragraph beginning on page 7 at line 15 with the following:

According to the structure, in a case where the memory element stores binary data ~~either of binary~~ such as light/light-off, one of~~either of~~ the switching elements ~~(for example, combination of a p type transistor and an n type transistor),~~ that~~which~~ make up the complementary inverter (for example, the combination of a p type transistor and an n type transistor), is conducted. Thus, even though the electric charge is stored in the optical modulation element in a certain display state, the left electric charge is emitted quickly via the conducted switching element, and the optical modulation element can shift to the next display state quickly. Thus, it is possible to restrict occurrence of a display error, or the burning and the deterioration of the optical modulation element.

Please replace the paragraph beginning on page 11 at line 12 with the following:

FIGs. 4A and 4B illustrate ~~is a~~ circuit diagrams showing ~~an~~ equivalent circuits of the pixel.

Please replace the paragraph beginning on page 11 at line 19 with the following:

FIG. 6 is an explanatory drawing showing the~~a~~ relationship of the parameter alpha (α) with the ~~between a combination of the~~ ON resistance value and [[/]]the OFF resistance value of the TFT ~~and the power consumption~~.

Please replace the paragraphs beginning on page 12 at line 2 to line 25 with the following:

FIG. 9 shows a ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 10 shows another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 11 shows still another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 12 shows another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 13 shows still another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 14 shows another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 15 shows still another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a pixel.

FIG. 16 shows another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of a display element.

Please replace the paragraph beginning on page 13 at line 1 with the following:

FIG. 17 shows still another ~~modification~~modified example of the embodiment, and is a circuit diagram showing a structure of an important part of adjacent pixels.

Please replace the paragraph beginning on page 13 at line 6 with the following:

FIG. 19 shows ~~another~~ prior art, and is a circuit diagram showing a structure of an important part of a pixel.

Please replace the paragraph beginning on page 13 at line 9 with the following:

FIG. 20 is a graph showing the change with~~a~~ time ~~change of a~~ of potential stored by a memory element, in the prior art pixel.

Please replace the paragraph beginning on page 14 at line 7 with the following:

Concretely, as described later, each of the pixels 4(i,j) includes a memory circuit 11 (described later), which stores whether the pixel 4(i,j) is ON or OFF. The memory circuit 11 is connected via the data line 2(j), to which the memory circuit 11 itself is connected, to the column address decoder 5, in a select period in which the row address decoder 6 is applying a potential, whose select level has been set in advance, to the select line 3(i), to which the memory circuit 11 itself is connected, and it is possible to access (read and write) the content of the memory circuit 11 from the column address decoder 5. Further, it is possible that the memory circuit 11 is separated from the data line 2(j) during a non-select period, which is a period other than a select period, and stores a value (ON or OFF) written in the select period, so as to continue to apply the value to the OLED 12 which functions as the optical modulation element.

Please replace the paragraph beginning on page 21 at line 20 with the following:

Here, in the case where the OLED 12 is ON, in the inverter 11a for driving the OLED 12, an equivalent circuit of a circuit for supplying a current to the OLED 12, as shown in FIG. 4A, has a structure in which a resistor Ron, connected to the reference potential Vref, is grounded via parallel circuits: a resistor Roff, a resistor Ro, and a capacitor Co. Note that, in the equivalent circuit of FIG. 4A, the inverter 11b, provided in the following stage, in which the gates of the TFTp3 and the TFTn4 function as the input ends, has higher input impedance, compared with the resistor Ron, the resistor Roff, the resistor Ro, and the capacitor Co, and does not influence the analysis of the power consumption, so that illustration thereof is omitted. Further, the resistor Ron and the resistor Roff[Ω] of FIG. 4A correspond to an ON resistor of the TFTp1 and an OFF resistor of the TFTn2, respectively. Further, the resistor Ro[Ω] and the capacitor Co[F] correspond to resistance component and capacitance component of the OLED 12.

Please replace the paragraph beginning on page 24 at line 19 with the following:

Further, when K•A is substituted for B (K•A = B) of the expression (2), and the relative value A, at a time when the parameter α is minimum, is calculated, the resultant is as follows.

$$d\alpha/dA = 1 - ((K + 1)/K^2) \bullet (1/A^2)$$
$$= 0 \quad \ldots (3)$$

This leads to the following expression (4).

$$A = (K + 1)^{1/2} /K \quad \ldots (4)$$

As a result, for example, in a case of K = 100, the ON resistance value Ron of the TFTp1 is set to be about as 0.10 times as large as the ON resistance Ro of the OLED 12, and in a case of K = 1000, the resistance Ron is set to be about as 0.032 times large as the resistance Ro, so that it is possible to minimize the power consumption in the pixel 4. Note that, as long as the increase of the power consumption, brought about by deviation from the most appropriate value, is within tolerance such as a few percent~~%,~~ , the ON resistance Ron may be set to be a bit away from the foregoing value.

Please replace the paragraph beginning on page 31 at line 10 with the following:

Further, when the OLED 12 lights, an equivalent circuit of a circuit for supplying a current, as shown ~~by ( )~~ in FIG. 4B, is a circuit in which the ground line Lg and the power line Lr of the equivalent circuit of the pixel 4 are replaced with each other. Thus, when the ON resistance of the TFTn2 is Ron and the OFF resistance of the TFTp1 is Roff, the expressions (1) to (4) are applied to the power consumption of the pixel 4a. Thus, when a ratio of the OFF resistance value Roff of the p type TFT with respect to the ON resistance value Ron of the n type TFT is K, the ratio A of the ON resistance value Ron of the n type TFT with respect to the ON resistance value Ro of the OLED 12 is set to be $(K + 1)^{1/2}/K$, so that it is possible to set the power consumption of the pixel 4a to be minimized.

Please replace the paragraph beginning on page 41 at line 18 with the following:

Further, in addition to the foregoing structure, it is preferable that the memory-integrated display element according to the present invention includes electric charge emitting circuit (the TFTp1 or the TFTn2 or the TFTp3 or the TFT[[p3]]n4) for emitting electric charge, stored in the optical modulation element while the memory element is applying a voltage to the optical modulation element, after application of the voltage is finished.